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An ISO/TS 16949, ISO 9001 and ISO 14001 Certified Company

## SILICON PLANAR POWER TRANSISTORS



CL100, A, B NPN CK100, A, B PNP

TO-39 Metal Can Package

# Medium Power Transistors Suitable for a wide Range of Medium Voltage and Current Amplifier Applications

 $R_{th\underline{(j-a)}}$ 

 $R_{th(j-c)}$ 

### **ABSOLUTE MAXIMUM RATINGS**

THERMAL CHARACTERISTICS

Junction to Ambient in free air

Junction to Case

DESCRIPTION	SYMBOL	VALUE	UNITS
Collector Emitter Voltage	V <sub>CER</sub>	50	V
Collector Base Voltage	V <sub>CBO</sub>	60	V
Emitter Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current - Continuous	I <sub>C</sub>	1.0	А
Power Dissipation@ T <sub>a</sub> =25°C	P <sub>D</sub>	0.8	W
Derate Above 25°C		4.57	mW/ °C
Power Dissipation@ T <sub>c</sub> =25°C	P <sub>D</sub>	4.0	W
Derate Above 25°C		22.73	mW/ °C
Operating And Storage Junction Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	- 65 to +200	°C

## ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
Collector Emitter Voltage	*V <sub>CER</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0	50			V
Collector Base Voltage	$V_{CBO}$	$I_{C}=100\mu A, I_{E}=0$	60			V
Emitter Base Voltage	$V_{EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector Cut Off Current	I <sub>CBO</sub>	$V_{CB}$ =40V, $I_{E}$ =0,			50	nA
Emitter Cut Off Current	I <sub>EBO</sub>	$V_{EB}=4V$ , $I_{E}=0$			1.0	μΑ
DC Current Gain	*h <sub>FE</sub>	$I_C=150$ mA, $V_{CE}=10$ V	40		300	
Collector Emitter Saturation Voltage	*V <sub>CE (sat)</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA			0.6	V
Base Emitter On Voltage	*V <sub>BE (on)</sub>	$I_C=150$ mA, $V_{CE}=1$ V			0.9	V

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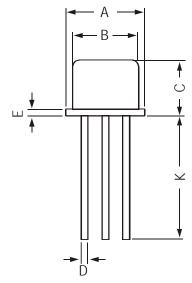
44

hFE Classification: A: 40 -120 B: 100 - 300

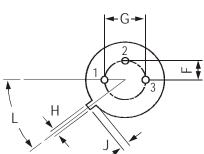
\*Pulsed: Pulse width <300ms, duty cycle <2%

## TO-39 Metal Can Package

# **TO-39 Metal Can Package**



	DIM	MIN	MAX		
	Α	8.50	9.39		
	В	7.74	8.50		
	С	6.09	6.60		
	D	0.40	0.53		
=	Ε		0.88		
Ē	F	2.41	2.66		
= = =	G	4.82	5.33		
All dimensions are in min	Н	0.71	0.86		
	J	0.73	1.02		
	Κ	12.70	1		
	L	42 DEG	48 DEG		
-	-				





PIN CONFIGURATION

- 1. EMITTER
- 2. BASE
- 3. COLLECTOR

# **Packing Details**

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-39	500 pcs/polybag	540 gm/500 pcs	3" x 7.5" x 7.5"	20K	17" x 15" x 13.5"	32K	40 kgs

**Notes** 

CL100, A, B NPN CK100, A, B PNP

TO-39 Metal Can Package

#### **Disclaimer**

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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